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DATASTAI

Advanced Search: INSPEC - 1969 to date (INZZ)

Search history:

| No. | Database | Search term | Info added since | Results | |
|-----|----------|--|------------------|---------|-----------------------------|
| 1 | INZZ | dual WITH gate SAME amorphous | unrestricted | 23 | show titles |
| 2 | INZZ | 1 AND perovskite | unrestricted | 0 | - |
| 3 | INZZ | (dual OR stacked) WITH gate AND perovskite | unrestricted | 0 | - |

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7/31/02

Select special search terms from the following list(s):

| EAST - [09.584601 - Dual Amorphous Monocrystalline Gate FET.wsp.1] | | | |
|--|---|---|---------------------|
| File Edit View Tools Window Help | | | |
| Search Text | | | |
| Hit# | Search Text | DB# | Time Stamp |
| 1 | 3757 257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:39 |
| 2 | 1150806 barium or strontium or titanium or lanthanum or zirconium or aluminum or STRONTIU or TITANIUM or LANTHANU or LLANTHANU or ZIRCONIUM or ALUMINUM | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:39 |
| 3 | 1647 ((fet or (field adj effect adj transistor)) and ((gate same amorphous) and (gate same \$4crystal\$4)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:39 |
| 4 | 0 ((fet or (field adj effect adj transistor)) and (gate same amorphous same \$4crystal\$4)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:37 |
| 5 | 1117 (dual with gate with layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:37 |
| 6 | 0 (dual with gate with layer) same (perovskite) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:37 |
| 7 | 2 (dual with gate with layer) same (silicon adj \$2oxide) same (strontium adj titanate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:37 |
| 8 | 3762 257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:39 |
| 9 | 1151252 barium or strontium or titanium or lanthanum or zirconium or aluminum or STRONTIU or TITANIUM or LANTHANU or LLANTHANU or ZIRCONIUM or ALUMINUM | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:40 |
| 10 | 75 ((dual with gate with layer)) and (257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls.) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/31 09:44 |
| 11 | 1327 ((fet or (field adj effect adj transistor)) and ((gate same amorphous) and (gate same (crystal\$4 or monocrystal\$4))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:45 |
| 12 | 1 ((dual with gate with layer)) and (257/52,410,411.ccls. 438/482,216,261,421,591,595,287,954,981.ccls.) and perovskite | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/30 10:46 |
| 13 | 46 ((dual or stacked) with gate) and perovskite | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2002/07/31 09:47 |
| End | | | |

updated EAST 7/31/02